MAX3232E 3-V to 5.5-V Multichannel RS-232 Line Driver and Receiver With ±15-kV IEC ESD Protection

1 Features

- ESD Protection for RS-232 Bus Pins
  - ±15 kV (HBM)
  - ±8 kV (IEC61000-4-2, Contact Discharge)
  - ±15 kV (IEC61000-4-2, Air-Gap Discharge)
- Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU V.28 Standards
- Operates With 3-V to 5.5-V V_{CC} Supply
- Operates up to 250 kbit/s
- Two Drivers and Two Receivers
- Low Supply Current: 300 μA (Typical)
- External Capacitors: 4 × 0.1 μF
- Accepts 5-V Logic Input With 3.3-V Supply
- Pin Compatible to Alternative High-Speed Devices (1 Mbit/s)
  - SN65C3232E (–40°C to +85°C)
  - SN75C3232E (0°C to 70°C)

2 Applications

- Battery-Powered Systems
- Notebooks
- Laptops
- Palmtop PCs
- Hand-Held Equipment

3 Description

The MAX3232E device consists of two line drivers, two-line receivers, and a dual charge-pump circuit with ±15-kV IEC ESD protection pin to pin (serial-port connection pins, including GND).

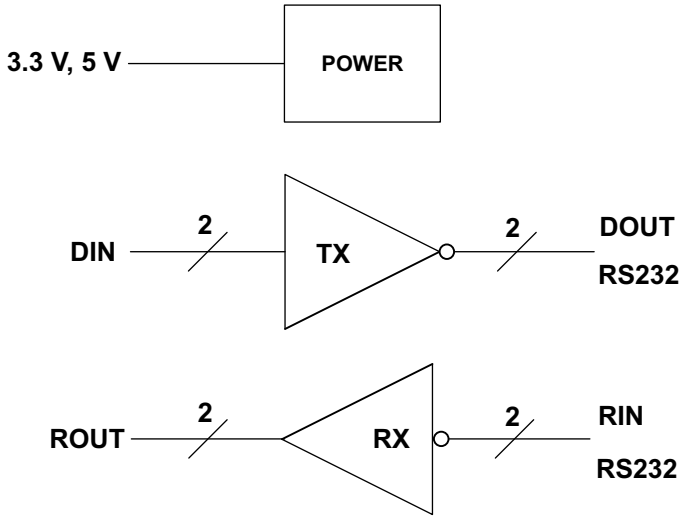
The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at data signaling rates up to 250 kbit/s and a maximum of 30-V/μs driver output slew rate.

Device Information[1]

PART NUMBER	PACKAGE	BODY SIZE (NOM)
MAX3232ExD	SOIC (16)	9.90 mm × 3.91 mm
MAX3232ExDB	SSOP (16)	6.20 mm × 5.30 mm
MAX3232ExDW	SOIC (16)	10.30 mm × 7.50 mm
MAX3232ExPW	TSSOP (16)	5.00 mm × 4.40 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Diagram



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision C (June 2015) to Revision D — **Page**

- Changed 3 V ± 5.5 V to 3 V to 5.5 V in the V_{CC} column of Table 3 ... 10

Changes from Revision B (December 2013) to Revision C — **Page**

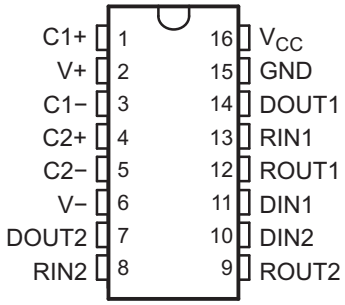
- Added *Device Information* table, *Pin Configuration and Functions* section, *ESD Ratings* table, *Feature Description* section, *Device Functional Modes*, *Application and Implementation* section, *Power Supply Recommendations* section, *Layout* section, *Device and Documentation Support* section, and *Mechanical, Packaging, and Orderable Information* section ... 1

Changes from Revision A (April 2007) to Revision B — **Page**

- Updated document to new TI data sheet format. ... 1
- Deleted *Ordering Information* table. ... 1
- Added *Thermal Information* table. ... 5

5 Pin Configuration and Functions

D, DW, DB and PW Package
16-Pin SOIC, SSOP and TSSOP
Top View



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
C1+	1	—	Positive lead of C1 capacitor
V+	2	O	Positive charge pump output for storage capacitor only
C1–	3	—	Negative lead of C1 capacitor
C2+	4	—	Positive lead of C2 capacitor
C2–	5	—	Negative lead of C2 capacitor
V–	6	O	Negative charge pump output for storage capacitor only
DOUT2	7	O	RS232 line data output (to remote RS232 system)
RIN2	8	I	RS232 line data input (from remote RS232 system)
ROUT2	9	O	Logic data output (to UART)
DIN2	10	I	Logic data input (from UART)
DIN1	11	I	Logic data input (from UART)
ROUT1	12	O	Logic data output (to UART)
RIN1	13	I	RS232 line data input (from remote RS232 system)
DOUT1	14	O	RS232 line data output (to remote RS232 system)
GND	15	—	Ground
V_{CC}	16	—	Supply Voltage, Connect to external 3-V to 5.5-V power supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage(2)		–0.3	6	V
V+	Positive output supply voltage(2)		–0.3	7	V
V–	Negative output supply voltage(2)		0.3	–7	V
V+ – V–	Supply voltage difference(2)			13	V
V_I	Input voltage	Drivers	–0.3	6	V
		Receivers	–25	25	V
V_O	Output voltage	Drivers	–13.2	13.2	V
		Receivers	–0.3	V_{CC} + 0.3	V
T_J	Operating virtual junction temperature			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to network GND.

6.2 ESD Ratings

				VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	All pins except RIN and DOUT	±2000	V
			RIN and DOUT Pins	±15,000	
		Charged-device model (CDM), per JEDEC specification JESD22-C101(2)	All pins	±1500	
		IEC61000-4-2, Contact Discharge	RS232 port pins (RIN, DOUT)	±8000	
		IEC61000-4-2, Air-Gap Discharge	RS232 port pins (RIN, DOUT)	±15,000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions(1)

See Figure 7.

				MIN	NOM	MAX	UNIT
	Supply voltage		V_{CC} = 3.3 V	3	3.3	3.6	V
			V_{CC} = 5 V	4.5	5	5.5	
V_{IH}	Driver high-level input voltage	DIN	V_{CC} = 3.3 V	2		5.5	V
			V_{CC} = 5 V	2.4		5.5	
V_{IL}	Driver low-level input voltage	DIN		0		0.8	V
V_I	Receiver input voltage	RIN		–25		25	V
T_A	Operating free-air temperature		MAX3232EC	0		70	°C
			MAX3232EI	–40		85	

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

6.4 Thermal Information

THERMAL METRIC[1]		MAX3232E				UNIT
		PW (TSSOP)	D (SOIC)	DW (SOIC)	DB (SSOP)	
		16 PINS	16 PINS	16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	99.3	76.1	72.3	90.9	°C/W
$R_{\theta JCtop}$	Junction-to-case (top) thermal resistance	20.8	36.7	33.5	36.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	45.1	33.6	37.1	43.8	°C/W
ψ_{JT}	Junction-to-top characterization parameter	0.6	4.2	7.5	4.2	°C/W
ψ_{JB}	Junction-to-board characterization parameter	45.1	33.3	37.1	42.9	°C/W
$R_{\theta JCbot}$	Junction-to-case (bottom) thermal resistance	–	–	–	–	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics — Device[1]

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 7).

PARAMETER		TEST CONDITIONS	MIN	TYP[2]	MAX	UNIT
I_{CC}	Supply current	No load, V_{CC} = 3.3 V or 5 V		0.3	1	mA

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

6.6 Electrical Characteristics — Driver[1]

over operating free-air temperature range (unless otherwise noted) (see Figure 7).

PARAMETER		TEST CONDITIONS		MIN	TYP[2]	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = GND	5	5.4		V
V_{OL}	Low-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = V_{CC}	–5	–5.4		V
I_{IH}	High-level input current	V_I = V_{CC}			±0.01	±1	μA
I_{IL}	Low-level input current	V_I at GND			±0.01	±1	μA
I_{OS}[3]	Short-circuit output current	V_{CC} = 3.6 V,	V_O = 0 V		±35	±60	mA
		V_{CC} = 5.5 V,	V_O = 0 V				
r_O	Output resistance	V_{CC}, V+, and V– = 0 V,	V_O = ±2 V	300	10M		Ω

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.
(2) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.
(3) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

6.7 Electrical Characteristics — Receiver[1]

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 7).

PARAMETER		TEST CONDITIONS	MIN	TYP[2]	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –1 mA	V_{CC} – 0.6	V_{CC} – 0.1		V
V_{OL}	Low-level output voltage	I_{OL} = 1.6 mA			0.4	V
V_{IT+}	Positive-going input threshold voltage	V_{CC} = 3.3 V		1.5	2.4	V
		V_{CC} = 5 V		1.8	2.4	
$V_{IT–}$	Negative-going input threshold voltage	V_{CC} = 3.3 V	0.6	1.2		V
		V_{CC} = 5 V	0.8	1.5		
V_{hys}	Input hysteresis (V_{IT+} – $V_{IT–}$)			0.3		V
r_i	Input resistance	V_I = ±3 V to ±25 V	3	5	7	kΩ

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

6.8 Switching Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 7)

PARAMETER		TEST CONDITIONS		MIN	TYP(2)	MAX	UNIT
	Maximum data rate	R_L = 3 kΩ, One DOUT switching,	C_L = 1000 pF, see Figure 3	150	250		kbit/s
$t_{sk(p)}$	Driver pulse skew(3)	R_L = 3 kΩ to 7 kΩ, see Figure 4	C_L = 150 pF to 2500 pF,		300		ns
SR(tr)	Driver slew rate, transition region (see Figure 3)	R_L = 3 kΩ to 7 kΩ, V_{CC} = 3.3 V	C_L = 150 pF to 1000 pF	6		30	V/μs
			C_L = 150 pF to 2500 pF	4		30	
t_{PLH}	Receiver propagation delay time, low- to high-level output	C_L = 150 pF, see Figure 5			300		ns
t_{PHL}	Receiver propagation delay time, high- to low-level output				300		ns
$t_{sk(p)}$	Receiver pulse skew(3)				300		ns

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(3) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

6.9 Typical Characteristics

V_{CC} = 3.3 V

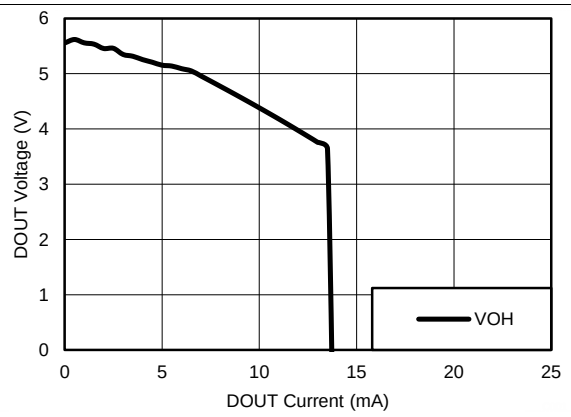


Figure 1. DOUT V_{OH} vs Load Current, Both Drivers Loaded

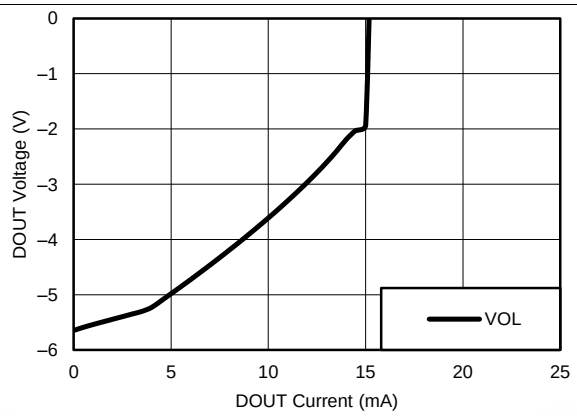
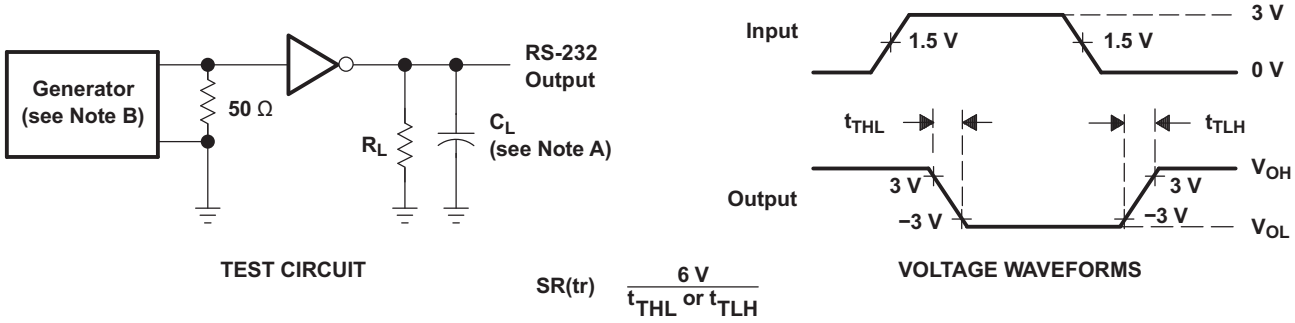


Figure 2. DOUT V_{OL} vs Load Current, Both Drivers Loaded

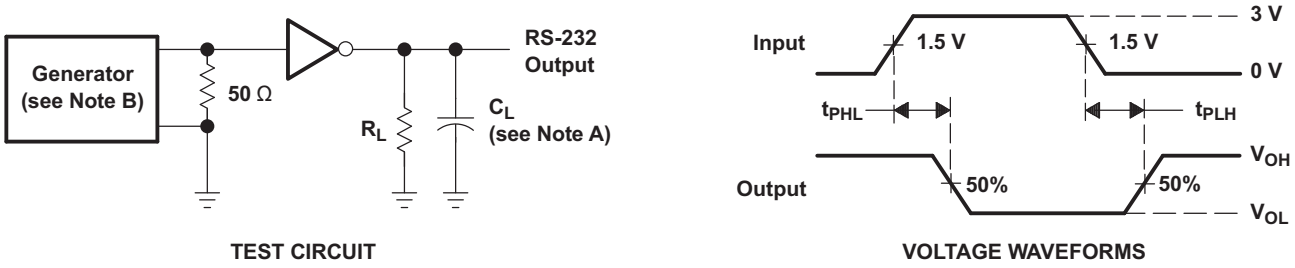
7 Parameter Measurement Information



A. C_L includes probe and jig capacitance

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns

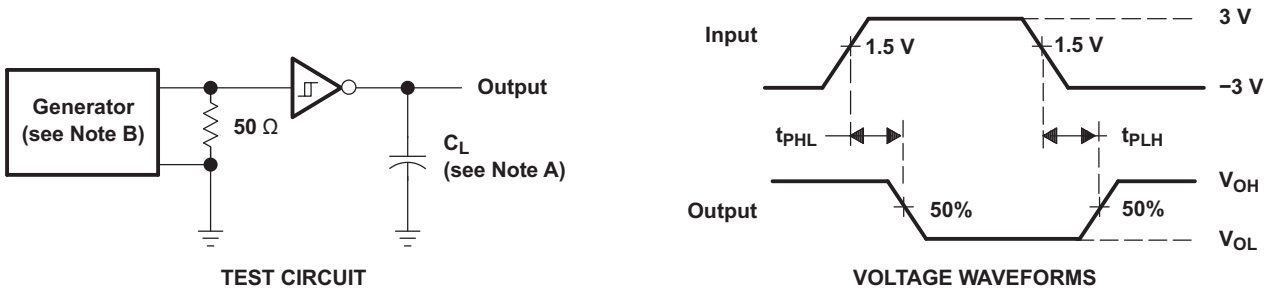
Figure 3. Driver Slew Rate



A. C_L includes probe and jig capacitance

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns

Figure 4. Driver Pulse Skew



A. C_L includes probe and jig capacitance

B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, t_r ≤ 10 ns, t_f ≤ 10 ns

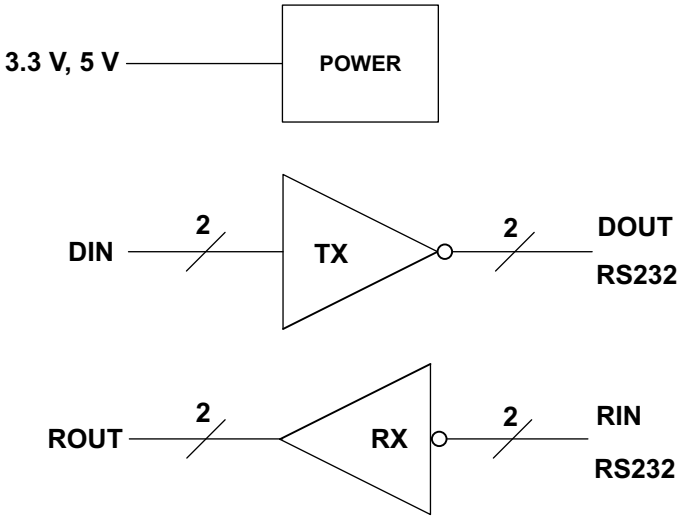
Figure 5. Receiver Propagation Delay Times

8 Detailed Description

8.1 Overview

The MAX3232E device consists of two line drivers, two-line receivers, and a dual charge-pump circuit with IEC61000-4-2 ESD protection terminal to terminal (serial-port connection terminals, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The device operates at data signaling rates up to 250 kbit/s and a maximum of 30-V/μs driver output slew rate. Outputs are protected against shorts to ground.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Power

The power block increases, inverts, and regulates voltage at V+ and V– pins using a charge pump that requires four external capacitors.

8.3.2 RS232 Driver

Two drivers interface standard logic level to RS232 levels. Both DIN inputs must be valid high or low.

8.3.3 RS232 Receiver

Two receivers interface RS232 levels to standard logic levels. An open input will result in a high output on ROUT. Each RIN input includes an internal standard RS232 load.

8.4 Device Functional Modes

Table 1 and Table 2 list the functional modes of the drivers and receivers of MAX3232E.

Table 1. Each Driver(1)

INPUT DIN	OUTPUT DOUT
L	H
H	L

(1) H = high level, L = low level

Table 2. Each Receiver(1)

INPUT RIN	OUTPUT ROUT
L	H
H	L
Open	H

(1) H = high level, L = low level,
Open = input disconnected or connected driver off

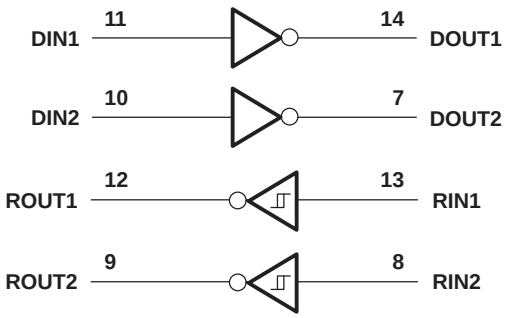


Figure 6. Logic Diagram

8.4.1 V_{CC} Powered by 3 V to 5.5 V

The device is in normal operation.

8.4.2 V_{CC} Unpowered, V_{CC} = 0 V

When MAX3232E is unpowered, it can be safely connected to an active remote RS232 device.

9 Application and Implementation

NOTE

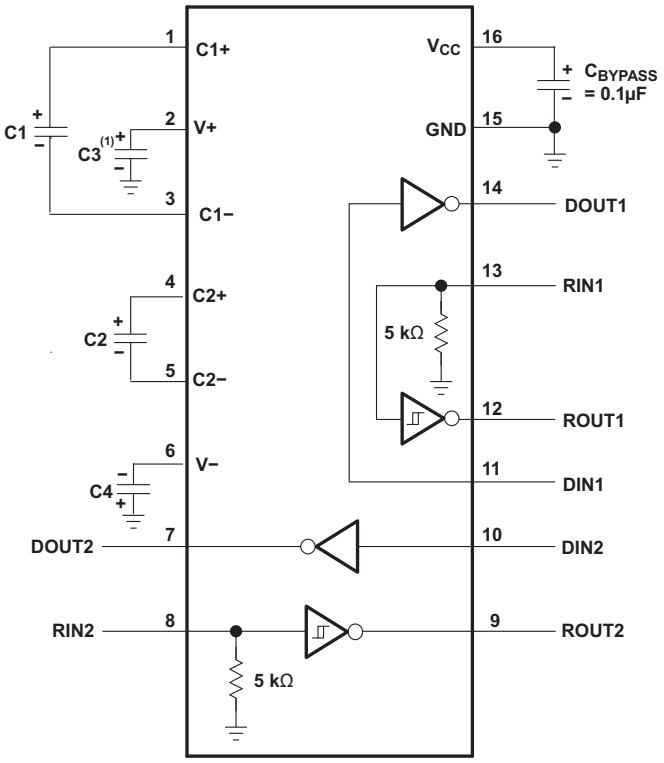
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

For proper operation, add capacitors as shown in Table 3.

9.2 Typical Application

ROUT and DIN connect to UART or general-purpose logic lines. RIN and DOUT lines connect to a RS232 connector or cable.



(1) C3 can be connected to V_{CC} or GND

Notes: A. Resistor values shown are nominal.

B. Nonpolorized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

Figure 7. Typical Operating Circuit and Capacitor Values

Table 3. VCC vs Capacitor Values

V_{CC}	C1	C2, C3, C4
3.3 V ± 0.3 V	0.1 µF	0.1 µF
5 V ± 0.5 V	0.047 µF	0.33 µF
3 V to 5.5 V	0.1 µF	0.47 µF

9.2.1 Design Requirements

The recommended V_{CC} is 3.3 V or 5 V. 3 V to 5.5 V is also possible

The maximum recommended bit rate is 250 kbit/s.

9.2.2 Detailed Design Procedure

All DIN inputs must be connected to valid low or high logic levels.

Select capacitor values based on V_{CC} level for best performance.

9.2.3 Application Curve

Figure 8 curves are for 3.3-V VCC and 250-kbit/s alternative bit data stream.

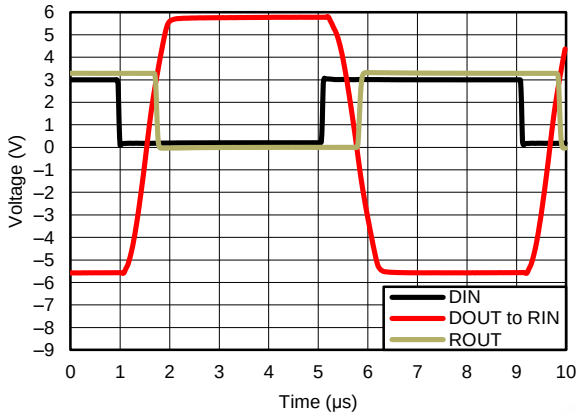


Figure 8. 250 kbit/s Driver to Receiver Loopback Timing Waveform, V_{CC}= 3.3 V

10 Power Supply Recommendations

The supply voltage, V_{CC}, should be between 3 V and 5.5 V. Select the values of the charge-pump capacitors using Table 3.

11 Layout

11.1 Layout Guidelines

Keep the external capacitor traces short, specifically on the C1 and C2 nodes that have the fastest rise and fall times.

11.2 Layout Example

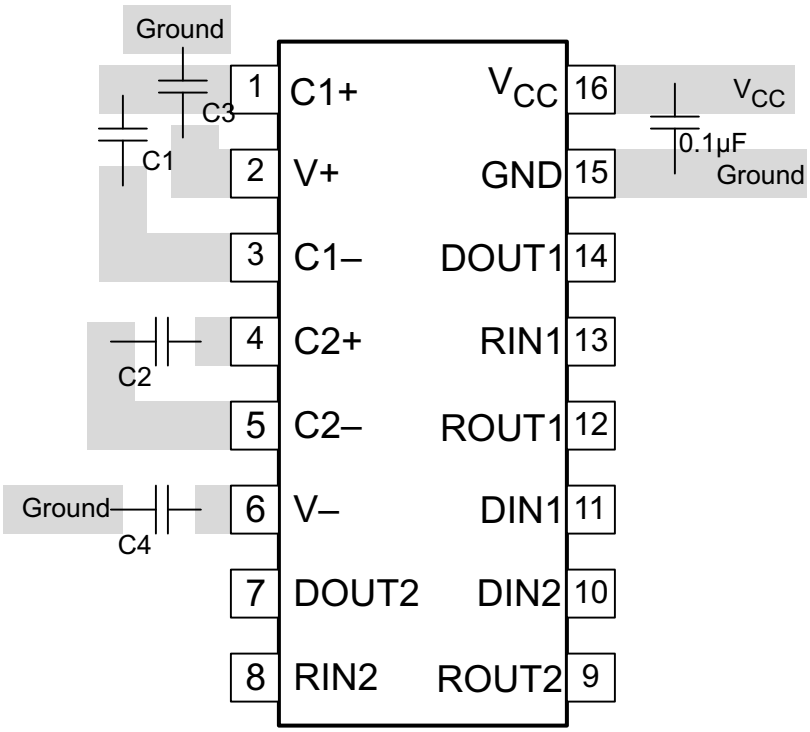


Figure 9. Layout Diagram

12 Device and Documentation Support

12.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.2 Trademarks

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.3 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.4 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
MAX3232ECD	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3232EC	Samples
MAX3232ECDB	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MP232EC	Samples
MAX3232ECDBG4	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MP232EC	Samples
MAX3232ECDBR	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MP232EC	Samples
MAX3232ECDE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3232EC	Samples
MAX3232ECDG4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3232EC	Samples
MAX3232ECDR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3232EC	Samples
MAX3232ECDRE4	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3232EC	Samples
MAX3232ECDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3232EC	Samples
MAX3232ECDWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3232EC	Samples
MAX3232ECDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3232EC	Samples
MAX3232ECPW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MP232EC	Samples
MAX3232ECPWE4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MP232EC	Samples
MAX3232ECPWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MP232EC	Samples
MAX3232EID	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3232EI	Samples
MAX3232EIDB	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP232EI	Samples
MAX3232EIDBE4	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP232EI	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
MAX3232EIDBG4	ACTIVE	SSOP	DB	16	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP232EI	Samples
MAX3232EIDBR	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP232EI	Samples
MAX3232EIDBRE4	ACTIVE	SSOP	DB	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP232EI	Samples
MAX3232EIDE4	ACTIVE	SOIC	D	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3232EI	Samples
MAX3232EIDR	ACTIVE	SOIC	D	16	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3232EI	Samples
MAX3232EIDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3232EI	Samples
MAX3232EIDWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3232EI	Samples
MAX3232EIDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3232EI	Samples
MAX3232EIPW	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP232EI	Samples
MAX3232EIPWE4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP232EI	Samples
MAX3232EIPWG4	ACTIVE	TSSOP	PW	16	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP232EI	Samples
MAX3232EIPWR	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP232EI	Samples
MAX3232EIPWRG4	ACTIVE	TSSOP	PW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP232EI	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF MAX3232E :

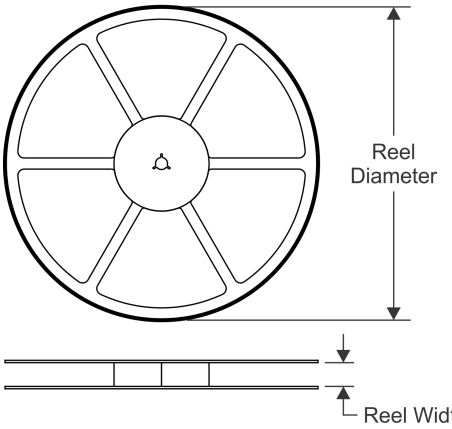
- Automotive: MAX3232E-Q1

NOTE: Qualified Version Definitions:

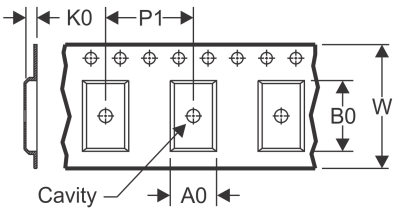
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

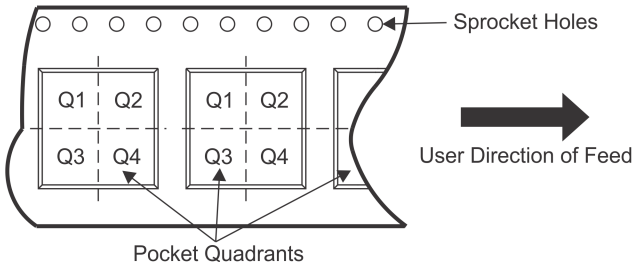


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

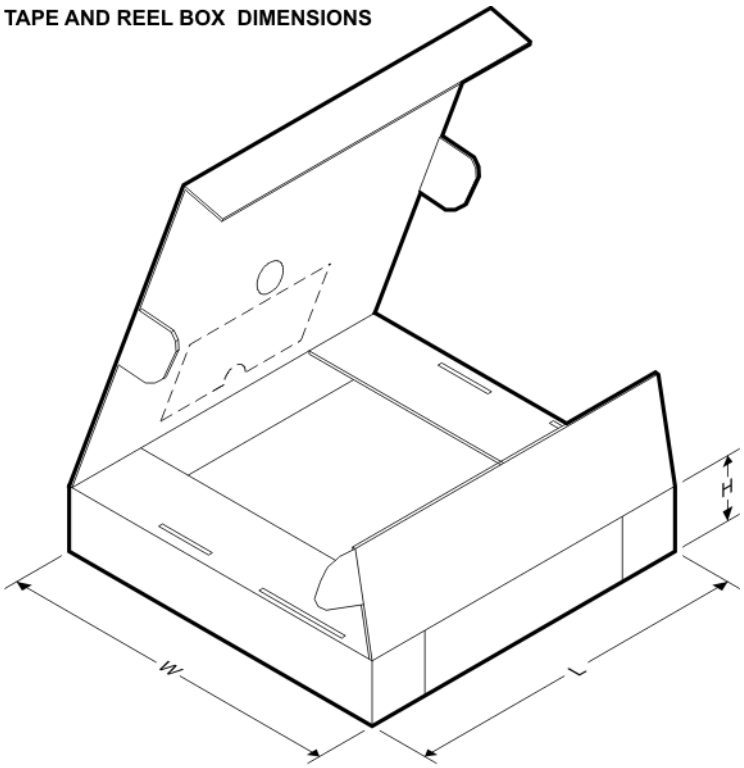
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
MAX3232ECDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
MAX3232ECDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
MAX3232ECPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
MAX3232EIDR	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1
MAX3232EIDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
MAX3232EIPWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
MAX3232ECDR	SOIC	D	16	2500	367.0	367.0	38.0
MAX3232ECDWR	SOIC	DW	16	2000	367.0	367.0	38.0
MAX3232ECPWR	TSSOP	PW	16	2000	367.0	367.0	35.0
MAX3232EIDR	SOIC	D	16	2500	367.0	367.0	38.0
MAX3232EIDWR	SOIC	DW	16	2000	367.0	367.0	38.0
MAX3232EIPWR	TSSOP	PW	16	2000	367.0	367.0	35.0

GENERIC PACKAGE VIEW

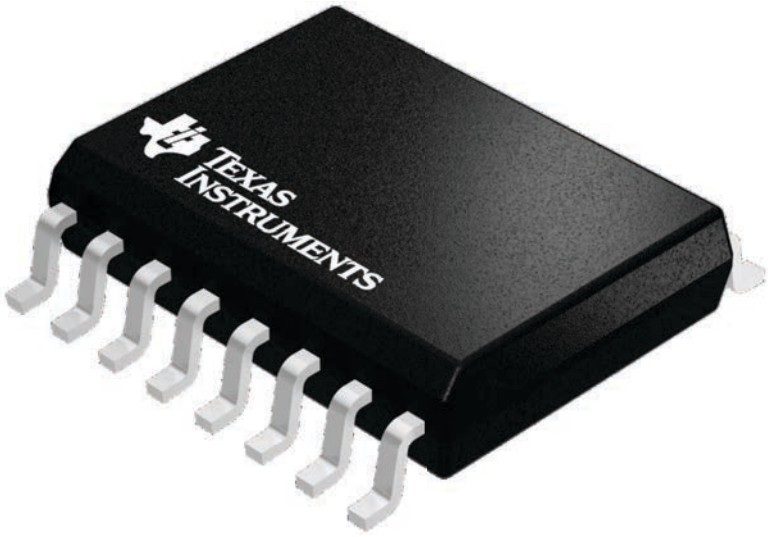
DW 16

SOIC - 2.65 mm max height

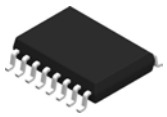
7.5 x 10.3, 1.27 mm pitch

SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4224780/A

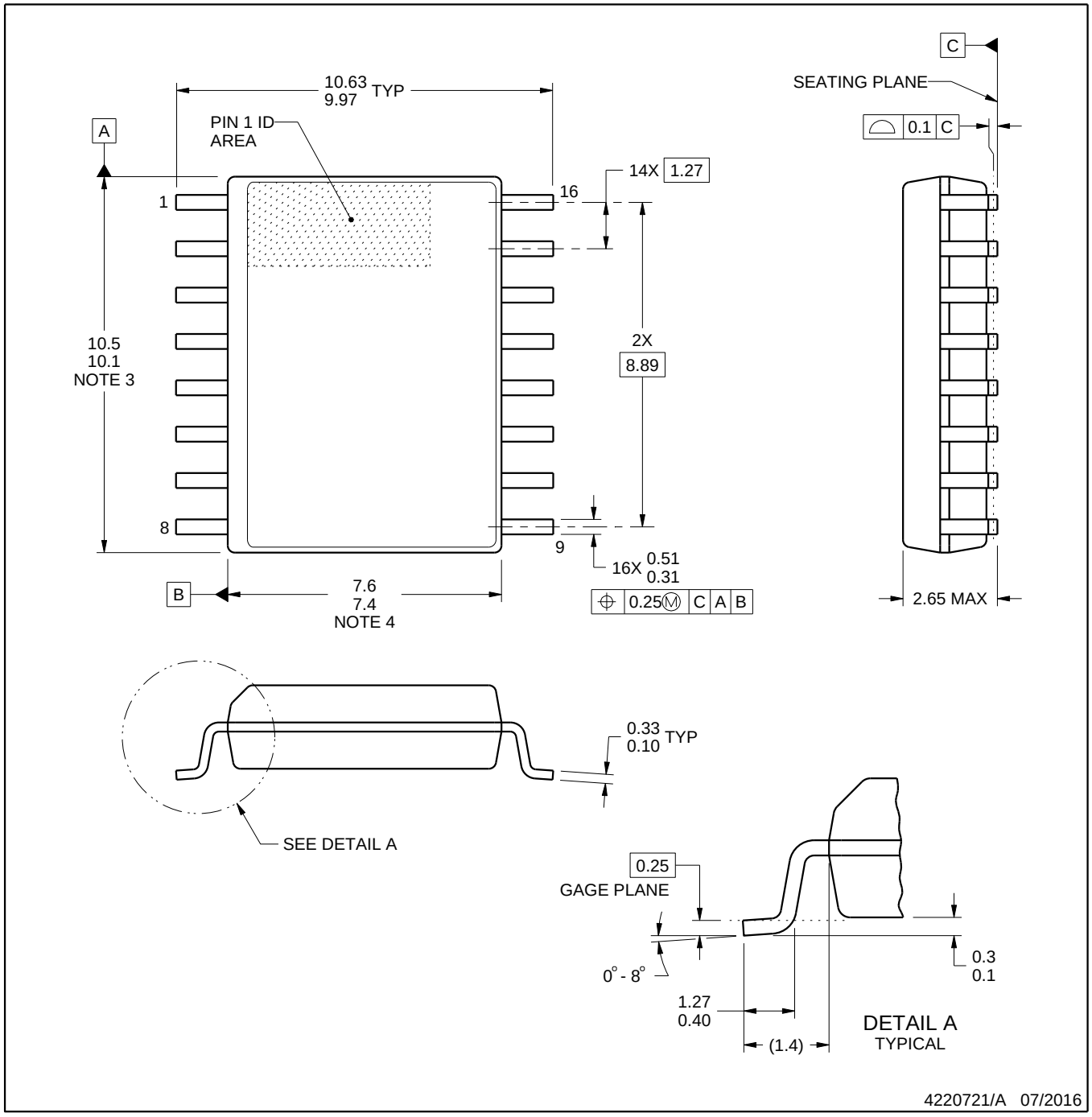


PACKAGE OUTLINE

DW0016A

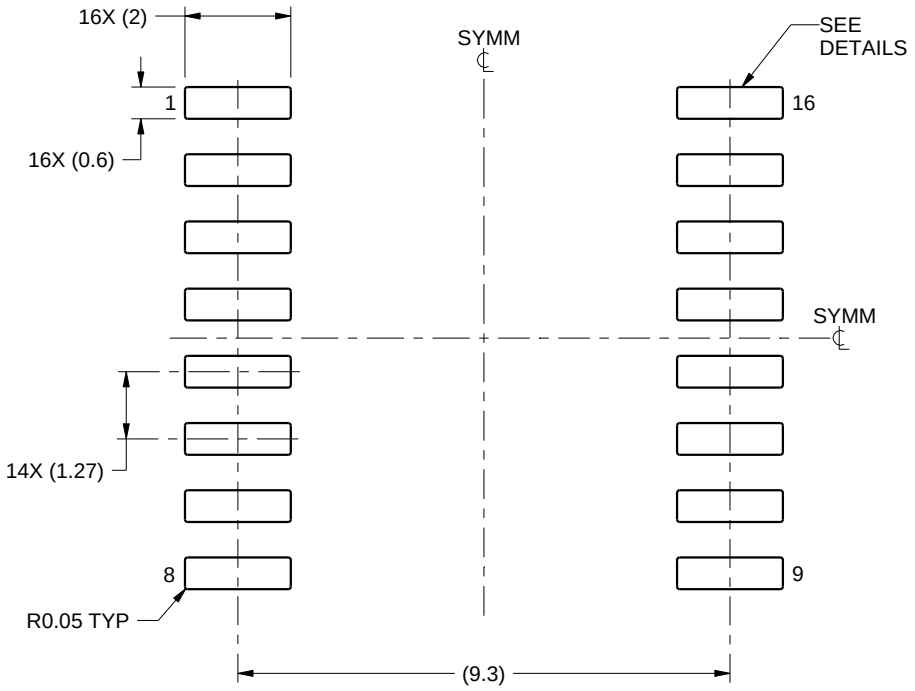
SOIC - 2.65 mm max height

SOIC

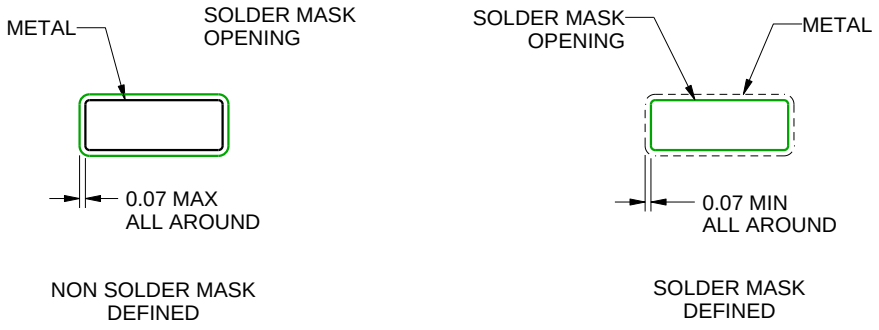


NOTES:

1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
5. Reference JEDEC registration MS-013.



LAND PATTERN EXAMPLE
SCALE:7X

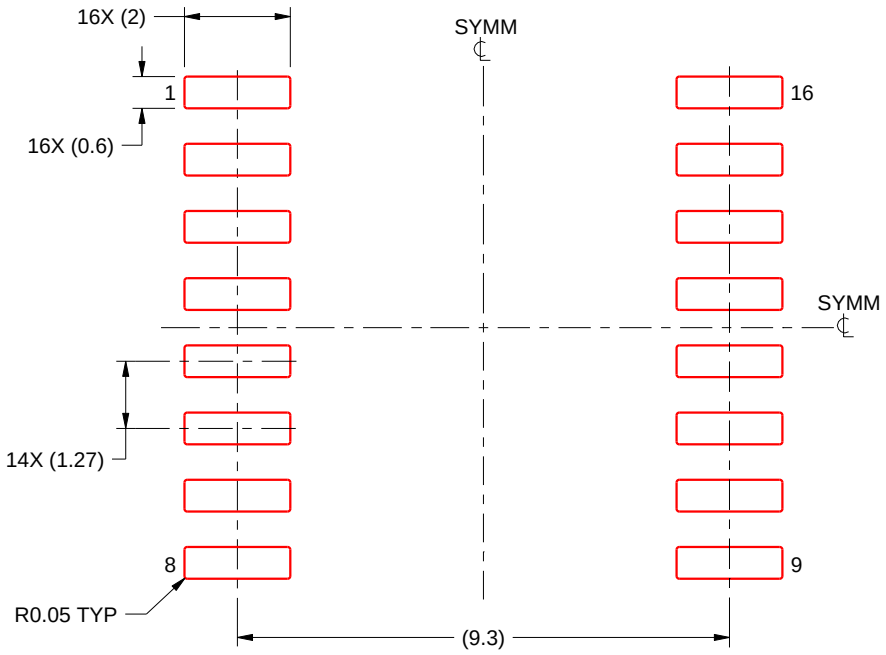


SOLDER MASK DETAILS

4220721/A 07/2016

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:7X

4220721/A 07/2016

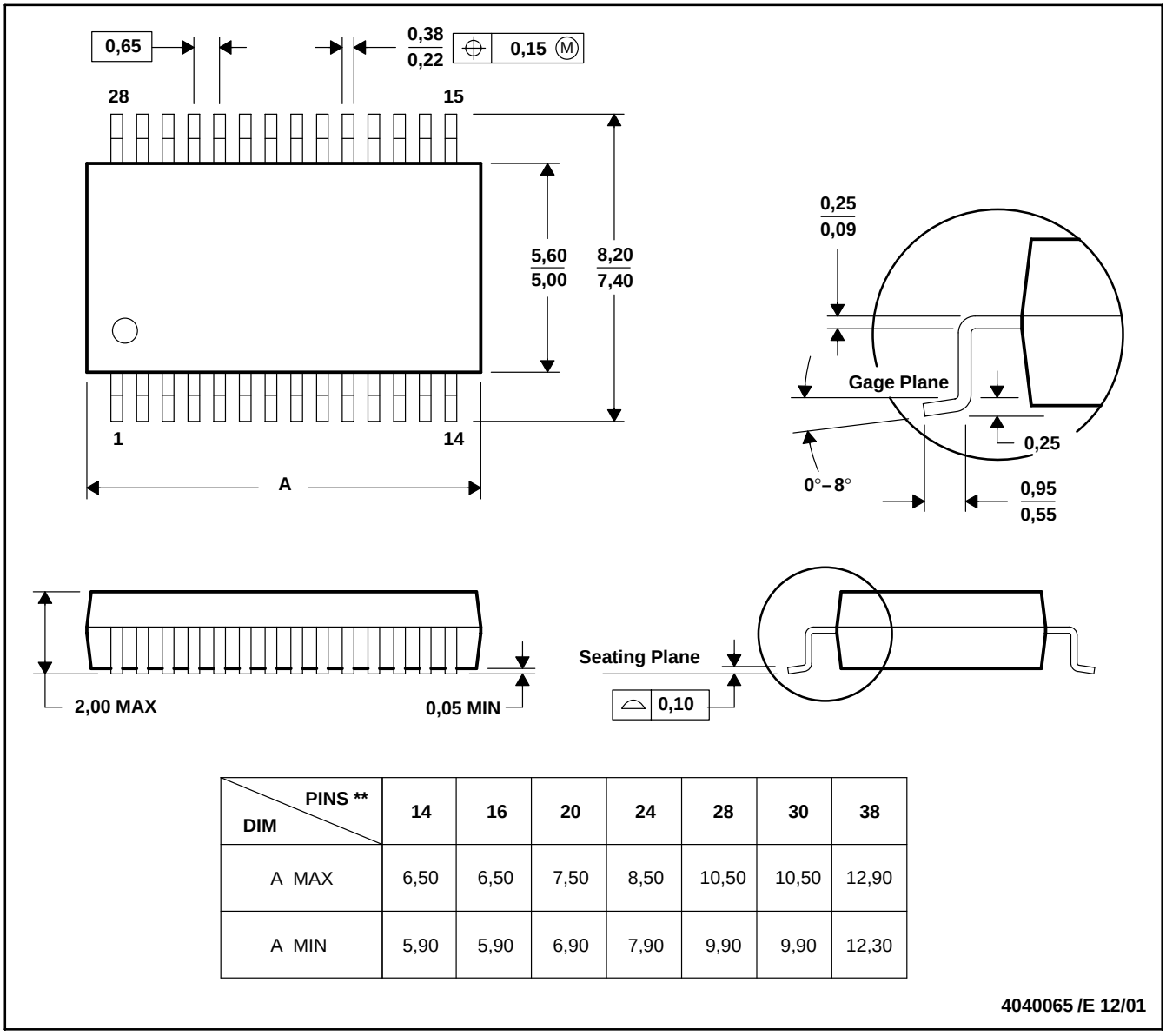
NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

MSSO002E – JANUARY 1995 – REVISED DECEMBER 2001

DB (R-PDSO-G)** **PLASTIC SMALL-OUTLINE**

28 PINS SHOWN



DIM \ PINS **	14	16	20	24	28	30	38
A MAX	6,50	6,50	7,50	8,50	10,50	10,50	12,90
A MIN	5,90	5,90	6,90	7,90	9,90	9,90	12,30

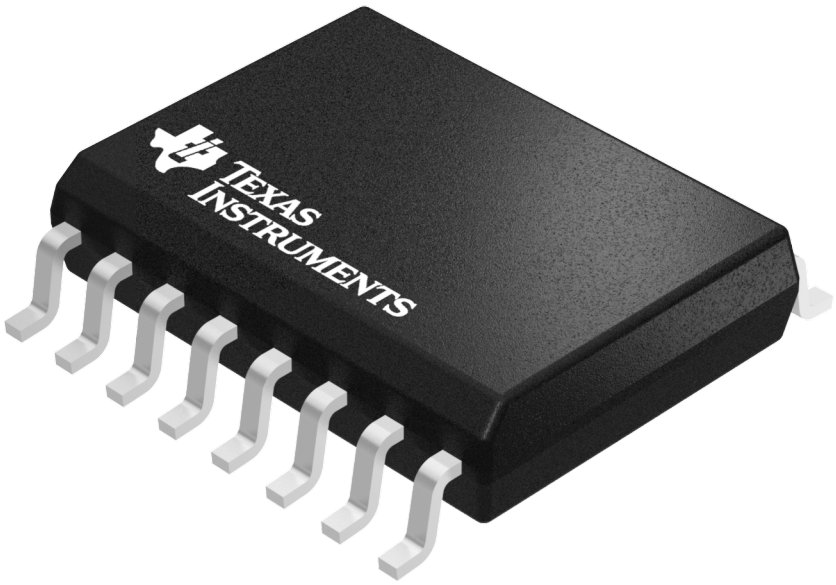
4040065 /E 12/01

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-150

GENERIC PACKAGE VIEW

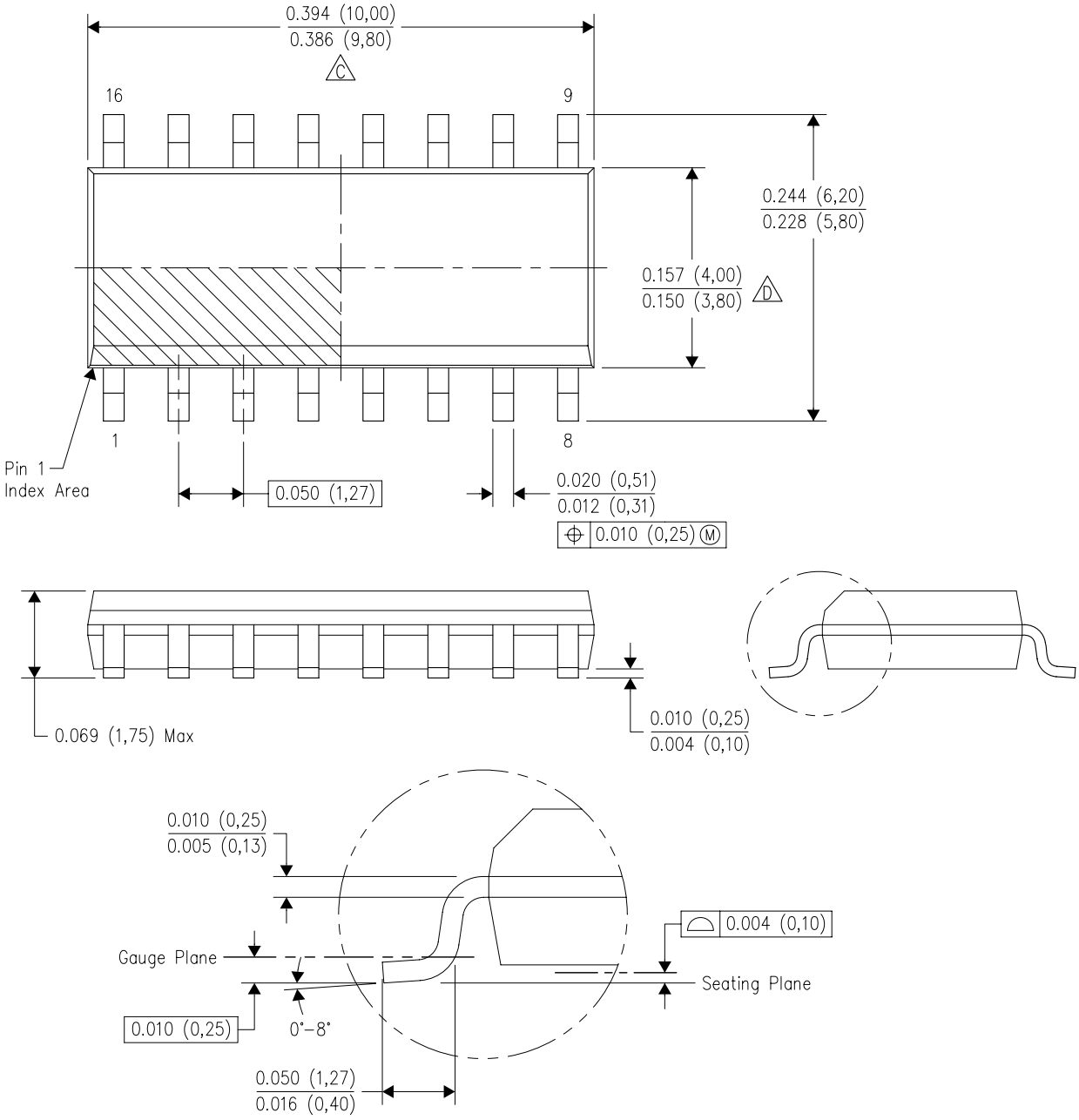
DW 16 SOIC - 2.65 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

D (R–PDSO–G16) PLASTIC SMALL OUTLINE



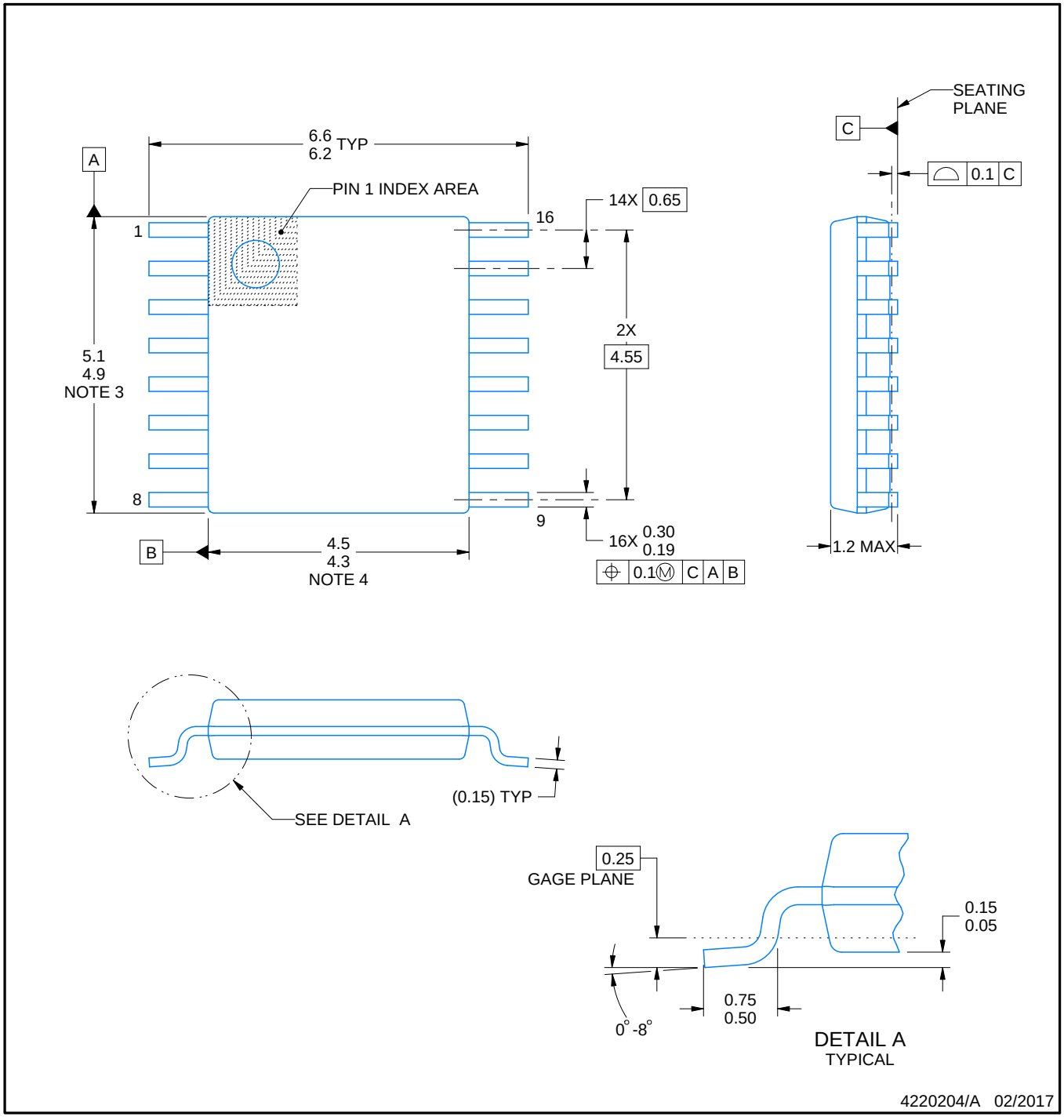
NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AC.

PACKAGE OUTLINE

PW0016A

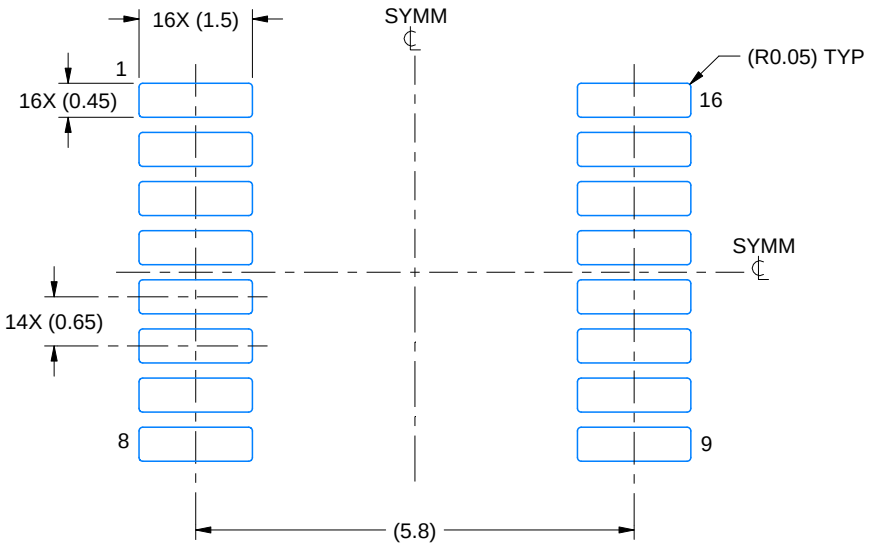
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

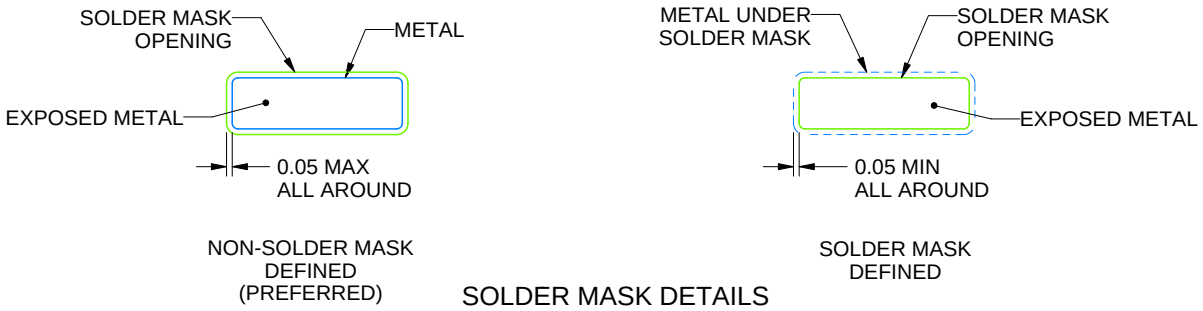


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

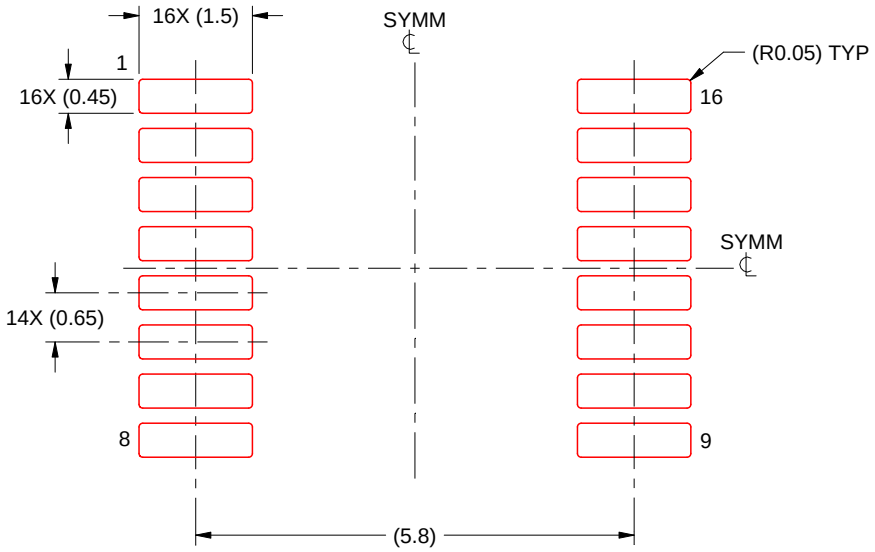


SOLDER MASK DETAILS

4220204/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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